

PSMN2R2-40PS

N-channel 40 V 2.1 mΩ standard level MOSFET 22 February 2013

Product data sheet

1. General description

Standard level N-channel MOSFET in TO220 package qualified to 175 °C. This product is designed and qualified for use in a wide range of industrial, communications and domestic equipment.

2. Features and benefits

- High efficiency due to low switching and conduction losses
- Suitable for standard level gate drive sources

3. Applications

- DC-to-DC convertors
- Load switching
- Motor control
- Server power supplies

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit		
V _{DS}	drain-source voltage	T _j ≥ 25 °C; T _j ≤ 175 °C		-	-	40	V		
I _D	drain current	T _{mb} = 25 °C; V _{GS} = 10 V; <u>Fig. 3</u> ; <u>Fig. 1</u>		-	-	100	Α		
P _{tot}	total power dissipation	T _{mb} = 25 °C; <u>Fig. 2</u>		-	-	306	W		
Static characteristics									
R _{DSon}	drain-source on-state resistance	$V_{GS} = 10 \text{ V}; I_D = 25 \text{ A}; T_j = 25 ^{\circ}\text{C};$ Fig. 12	[1]	-	1.75	2.1	mΩ		
Dynamic chara	Dynamic characteristics								
Q_{GD}	gate-drain charge	V_{GS} = 10 V; I_D = 80 A; V_{DS} = 20 V; Fig. 14; Fig. 15		-	25	-	nC		

[1] Measured 3 mm from package.



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5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate	mb	D I
2	D	drain	 	
3	S	source		G C
mb	D	drain	ij	mbb076 S
			TO-220AB (SOT78)	

6. Ordering information

Table 3. Ordering information

Type number	Package					
	Name	Description	Version			
PSMN2R2-40PS	TO-220AB	plastic single-ended package; heatsink mounted; 1 mounting hole; 3-lead TO-220AB	SOT78			

7. Marking

Table 4. Marking codes

Type number	Marking code
PSMN2R2-40PS	PSMN2R2-40PS

8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V _{DS}	drain-source voltage	T _j ≥ 25 °C; T _j ≤ 175 °C	-	40	V
V_{DGR}	drain-gate voltage	$T_j \ge 25$ °C; $T_j \le 175$ °C; $R_{GS} = 20$ kΩ	-	40	V
V_{GS}	gate-source voltage		-20	20	V
I _D	drain current	V _{GS} = 10 V; T _{mb} = 100 °C; <u>Fig. 1</u>	-	100	Α
		V _{GS} = 10 V; T _{mb} = 25 °C; <u>Fig. 3</u> ; <u>Fig. 1</u>	-	100	Α
I _{DM}	peak drain current	pulsed; $t_p \le 10 \mu s$; $T_{mb} = 25 ^{\circ}C$; <u>Fig. 3</u>	-	1122	Α

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Symbol	Parameter	Conditions	Min	Max	Unit
P _{tot}	total power dissipation	T _{mb} = 25 °C; <u>Fig. 2</u>	-	306	W
T _{stg}	storage temperature		-55	175	°C
T _j	junction temperature		-55	175	°C
Source-drain	1 diode				,
I _S	source current	T _{mb} = 25 °C	-	100	Α
I _{SM}	peak source current	pulsed; $t_p \le 10 \ \mu s$; $T_{mb} = 25 \ ^{\circ}C$	-	1122	Α
Avalanche ru	uggedness				
E _{DS(AL)S}	non-repetitive drain-source avalanche energy	V_{GS} = 10 V; $T_{j(init)}$ = 25 °C; I_D = 100 A; $V_{sup} \le$ 40 V; unclamped; R_{GS} = 50 Ω	-	1.24	J

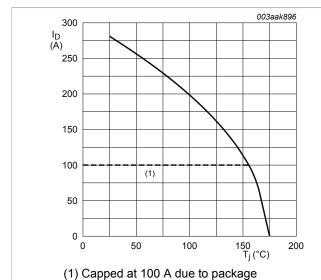


Fig. 1. Continuous drain current as a function of mounting base temperature

 $V_{GS} \ge 10V$

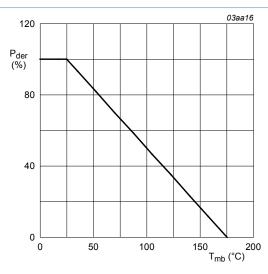


Fig. 2. Normalized total power dissipation as a function of mounting base temperature

$$P_{der} = \frac{P_{tot}}{P_{tot(25^{\circ}\text{C})}} \times 100 \,\%$$

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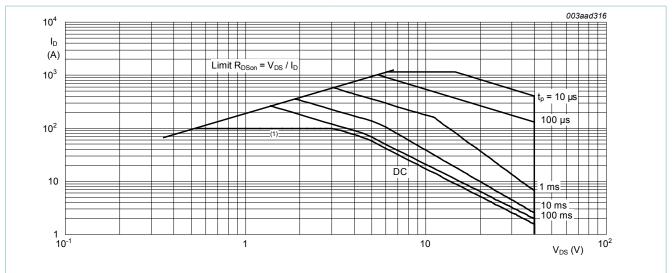


Fig. 3. Safe operating area; continuous and peak drain currents as a function of drain-source voltage

 $T_{mb} = 25$ °C; I_{DM} is a single pulse; (1) Capped at 100 A due to package

9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R _{th(j-mb)}	thermal resistance from junction to mounting base	Fig. 4	-	0.25	0.5	K/W

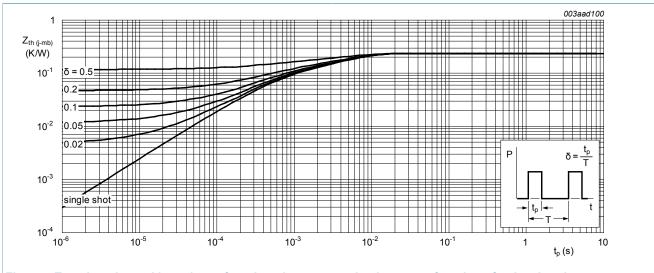


Fig. 4. Transient thermal impedance from junction to mounting base as a function of pulse duration

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10. Characteristics

Table 7. Characteristics

Tested to JEDEC standards where applicable.

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
Static chara	acteristics						
` '		I _D = 250 μA; V _{GS} = 0 V; T _j = -55 °C		36	-	-	V
	breakdown voltage	I _D = 250 μA; V _{GS} = 0 V; T _j = 25 °C		40	-	-	V
$V_{GS(th)}$	gate-source threshold voltage	$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = -55 \text{ °C};$ Fig. 10		-	-	4.6	V
		$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 175 \text{ °C};$ Fig. 10		1	-	-	V
		I _D = 1 mA; V _{DS} = V _{GS} ; T _j = 25 °C; Fig. 11; Fig. 10		2	3	4	V
I _{DSS}	drain leakage current	V _{DS} = 40 V; V _{GS} = 0 V; T _j = 25 °C		-	-	10	μA
		V _{DS} = 40 V; V _{GS} = 0 V; T _j = 125 °C		-	-	200	μΑ
I _{GSS}	gate leakage current	V _{GS} = 20 V; V _{DS} = 0 V; T _j = 25 °C		-	-	100	nA
		V _{GS} = -20 V; V _{DS} = 0 V; T _j = 25 °C		-	-	100	nA
R _{DSon} drain-source on-st resistance	drain-source on-state resistance	V _{GS} = 10 V; I _D = 25 A; T _j = 100 °C; Fig. 12; Fig. 13		-	2.4	2.85	mΩ
		V _{GS} = 10 V; I _D = 25 A; T _j = 175 °C; Fig. 12; Fig. 13		-	3.25	3.9	mΩ
		V_{GS} = 10 V; I_D = 25 A; T_j = 25 °C; Fig. 12	[1]	-	1.75	2.1	mΩ
R_G	internal gate resistance (AC)	f = 1 MHz		-	1	-	Ω
Dynamic ch	aracteristics		1		'		
Q _{G(tot)}	total gate charge	I _D = 0 A; V _{DS} = 0 V; V _{GS} = 10 V		-	110	-	nC
		I _D = 80 A; V _{DS} = 20 V; V _{GS} = 10 V;		-	130	-	nC
Q _{GS}	gate-source charge	Fig. 14; Fig. 15		-	42	-	nC
Q _{GS(th)}	pre-threshold gate- source charge			-	24	-	nC
Q _{GS(th-pl)}	post-threshold gate- source charge			-	18	-	nC
Q_{GD}	gate-drain charge			-	25	-	nC
$V_{GS(pl)}$	gate-source plateau voltage	I _D = 80 A; V _{DS} = 20 V; <u>Fig. 14</u> ; <u>Fig. 15</u>		-	4.95	-	V
C _{iss}	input capacitance	$V_{DS} = 20 \text{ V}; V_{GS} = 0 \text{ V}; f = 1 \text{ MHz};$ $T_j = 25 \text{ °C}; Fig. 16$		-	8423	-	pF
C _{oss}	output capacitance			-	1671	-	pF

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Symbol	Parameter	Conditions		Min	Тур	Max	Unit
C _{rss}	reverse transfer capacitance			-	814	-	pF
t _{d(on)}	turn-on delay time	V_{DS} = 20 V; R_L = 0.25 Ω ; V_{GS} = 10 V;		-	33.2	-	ns
t _r	rise time	$R_{G(ext)} = 1.5 \Omega$		-	40.4	-	ns
t _{d(off)}	turn-off delay time			-	66.6	-	ns
t _f	fall time			-	25.2	-	ns
Source-dra	in diode			I			
V _{SD}	source-drain voltage	$I_S = 25 \text{ A}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C}; Fig. 17$		-	0.85	1.2	V
t _{rr}	reverse recovery time	I_S = 25 A; dI_S/dt = -100 A/ μ s; V_{GS} = 0 V; V_{DS} = 20 V		-	53.7	-	ns
Q _r	recovered charge	I_S = 25 A; dI_S/dt = -100 A/ μ s; V_{GS} = 0 V; V_{DS} = 20 V; T_j = 25 °C		-	80.75	-	nC

[1] Measured 3 mm from package.

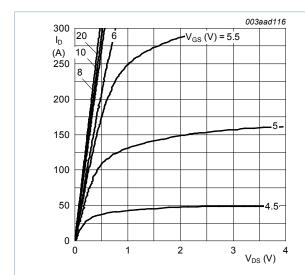


Fig. 5. Output characteristics: drain current as a function of drain-source voltage; typical values



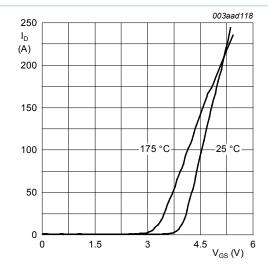


Fig. 6. Transfer characteristics: drain current as a function of gate-source voltage; typical values

$$V_{DS} > I_D \times R_{DSon}$$

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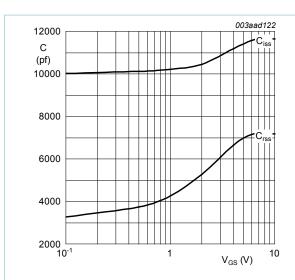


Fig. 7. Input and reverse transfer capacitances as a function of gate-source voltage; typical values

$$V_{DS}=0\,V; f=1MHz$$

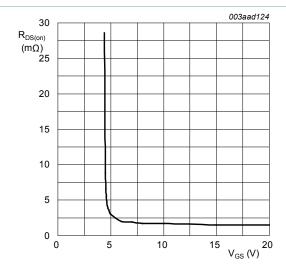


Fig. 9. Drain-source on-state resistance as a function of gate-source voltage; typical values

$$T_j = 25$$
 °C; $I_D = 25$ A

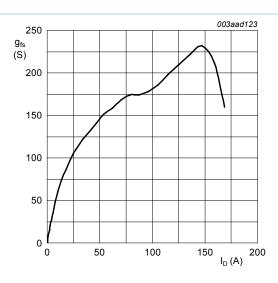


Fig. 8. Forward transconductance as a function of drain current; typical values

$$T_j = 25 \,^{\circ}C; V_{DS} = 25 V$$

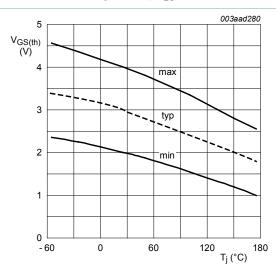


Fig. 10. Gate-source threshold voltage as a function of junction temperature

$$I_D = 1 \text{ mA}; V_{DS} = V_{GS}$$

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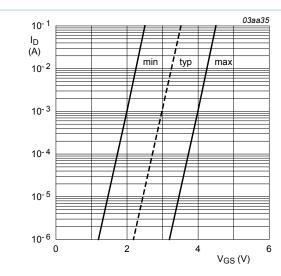


Fig. 11. Sub-threshold drain current as a function of gate-source voltage

$$T_j = 25 \,^{\circ}C; V_{DS} = 5V$$

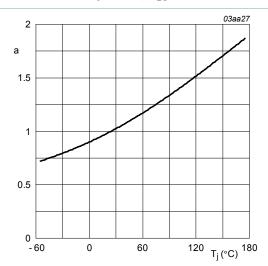


Fig. 13. Normalized drain-source on-state resistance factor as a function of junction temperature

$$a = \frac{R_{DSon}}{R_{DSon(25^{\circ}C)}}$$

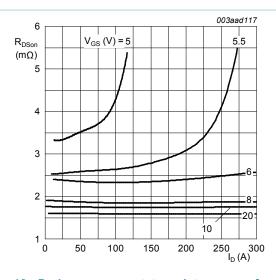


Fig. 12. Drain-source on-state resistance as a function of drain current; typical values

$$T_j = 25 \,^{\circ}C$$

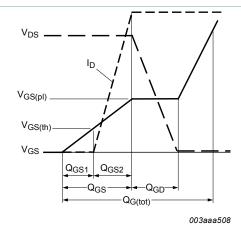


Fig. 14. Gate charge waveform definitions

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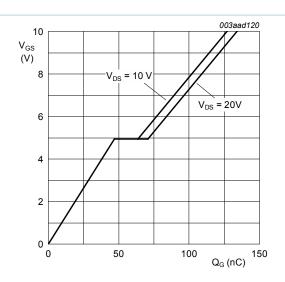


Fig. 15. Gate-source voltage as a function of gate charge; typical values

$$T_j = 25$$
 °C; $I_D = 25$ A

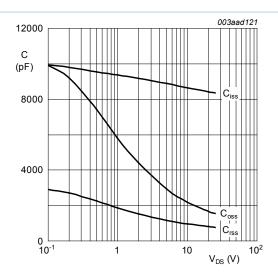


Fig. 16. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

$$V_{GS} = 0V; f = 1MHz$$

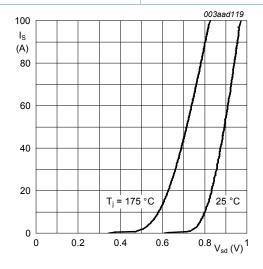
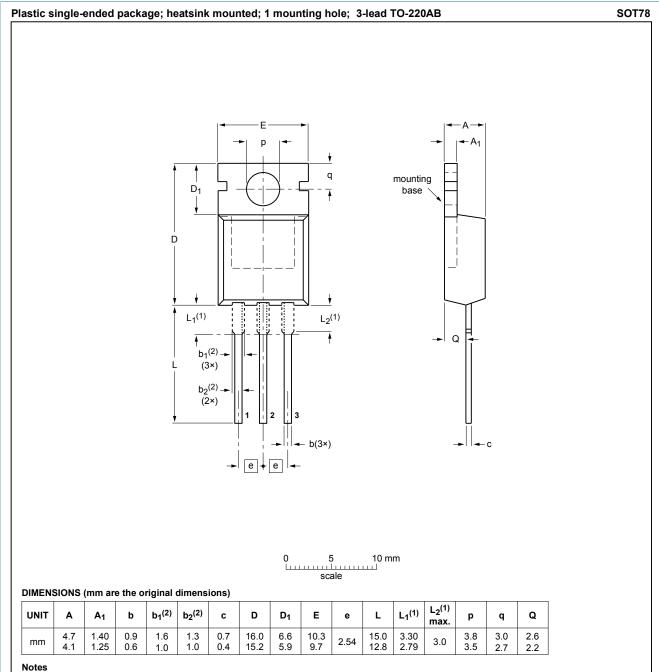


Fig. 17. Source current as a function of source-drain voltage; typical values

$$V_{GS} = 0 V$$

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11. Package outline



- 1. Lead shoulder designs may vary.
- Dimension includes excess dambar.

OUTLINE		REFER	ENCES	EUROPEAN	ISSUE DATE
VERSION	IEC	JEDEC	JEITA	PROJECTION	1330E DATE
SOT78		3-lead TO-220AB	SC-46		08-04-23 08-06-13

Fig. 18. Package outline TO-220AB (SOT78)

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